

AOD410

N-Channel Enhancement Mode Field Effect Transistor

General Description

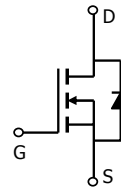
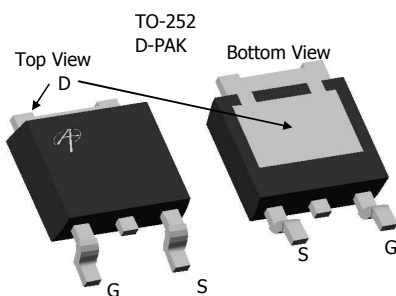
The AOD410 uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. This device is suitable for use as a load switch or in PWM applications.

- RoHS Compliant
- Halogen Free*

Features

$V_{DS} (V) = 30V$
 $I_D = 8A (V_{GS} = 10V)$
 $R_{DS(ON)} < 65m\Omega (V_{GS} = 10V)$
 $R_{DS(ON)} < 105m\Omega (V_{GS} = 4.5V)$

100% UIS Tested!
100% Rg Tested!



Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ^G	I_D	$T_C=25^\circ C$	8
		$T_C=100^\circ C$	6
Pulsed Drain Current ^B	I_{DM}	20	A
Avalanche Current ^C	I_{AR}	8	A
Repetitive avalanche energy $L=0.1mH$ ^C	E_{AR}	10	mJ
Power Dissipation ^B	P_D	$T_C=25^\circ C$	25
		$T_C=100^\circ C$	12.5
Power Dissipation ^A	P_{DSM}	$T_A=25^\circ C$	2.1
		$T_A=70^\circ C$	1.33
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 175	$^\circ C$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	20	30	$^\circ C/W$
Maximum Junction-to-Ambient ^A		Steady-State	46	60
Maximum Junction-to-Case ^C	$R_{\theta JL}$	5.3	7	$^\circ C/W$

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V	30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =24V, V _{GS} =0V T _J =55°C			1 5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} = ±20V			100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} I _D =250μA	1	1.8	3	V
I _{D(ON)}	On state drain current	V _{GS} =4.5V, V _{DS} =5V	10			A
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =8A T _J =125°C		48 76	65 100	mΩ
		V _{GS} =4.5V, I _D =2A		75	105	mΩ
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =8A		6.2		S
V _{SD}	Diode Forward Voltage	I _S =1A, V _{GS} =0V		0.75	1	V
I _S	Maximum Body-Diode Continuous Current				4.3	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =15V, f=1MHz		288		pF
C _{oss}	Output Capacitance			57		pF
C _{riss}	Reverse Transfer Capacitance			39		pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz		3		Ω
SWITCHING PARAMETERS						
Q _g (10V)	Total Gate Charge	V _{GS} =10V, V _{DS} =15V, I _D =8A		6.72		nC
Q _g (4.5V)	Total Gate Charge			3.34		nC
Q _{gs}	Gate Source Charge			0.76		nC
Q _{gd}	Gate Drain Charge			1.78		nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =10V, V _{DS} =15V, R _L =1.8Ω, R _{GEN} =3Ω		3.7		ns
t _r	Turn-On Rise Time			3.7		ns
t _{D(off)}	Turn-Off DelayTime			15.6		ns
t _f	Turn-Off Fall Time			2.6		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =8A, di/dt=100A/μs		12.6		ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =8A, di/dt=100A/μs		5.1		nC

A: The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The Power dissipation P_{DSM} is based on R_{θJA} and the maximum allowed junction temperature of 150°C. The value in any a given application depends on the user's specific board design, and the maximum temperature for 175°C may be used if the PCB allows it.

B. The power dissipation P_D is based on T_{J(MAX)}=175°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C: Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=175°C.

D. The R_{θJA} is the sum of the thermal impedance from junction to case R_{θJC} and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300 μs pulses, duty cycle 0.5% max.

F. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The SOA curve provides a single pulse rating.

G. The maximum current rating is limited by bond-wires.

*This device is guaranteed green after data code 8X11 (Sep 1ST 2008).

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

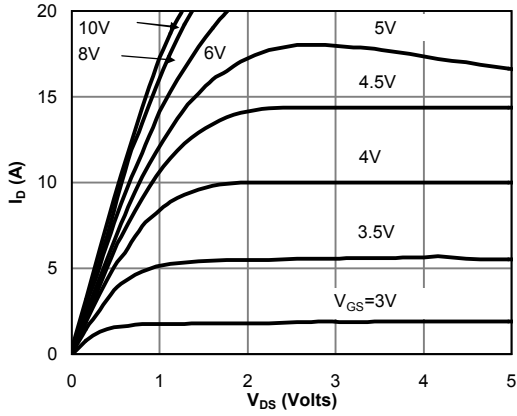


Fig 1: On-Region Characteristics

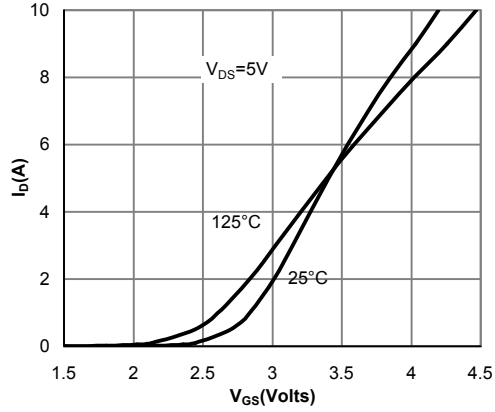


Figure 2: Transfer Characteristics

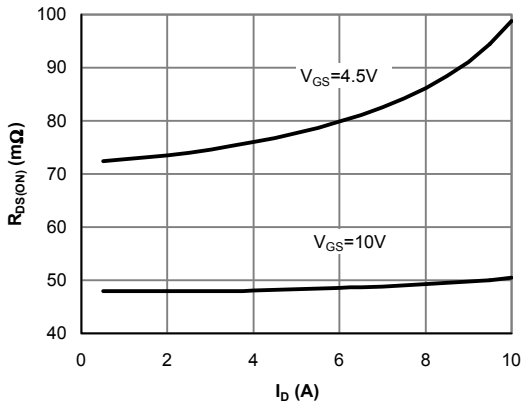


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

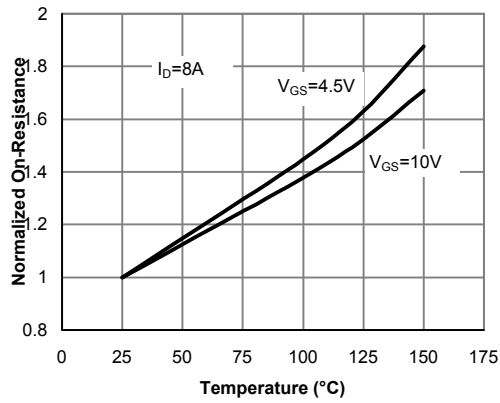


Figure 4: On-Resistance vs. Junction Temperature

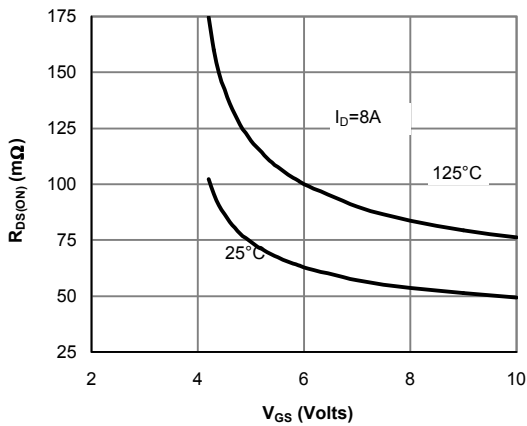


Figure 5: On-Resistance vs. Gate-Source Voltage

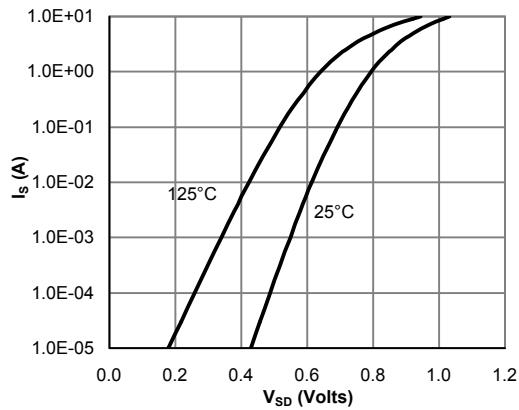


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

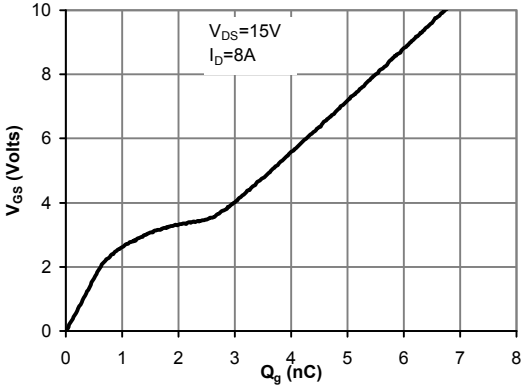


Figure 7: Gate-Charge Characteristics

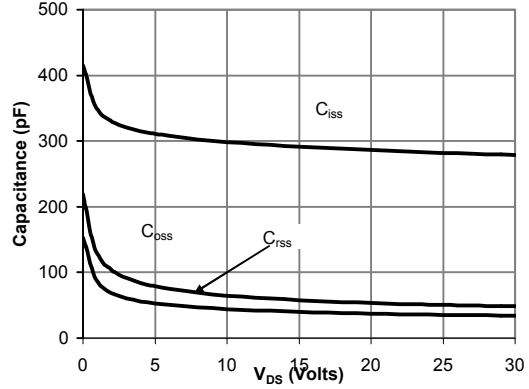


Figure 8: Capacitance Characteristics

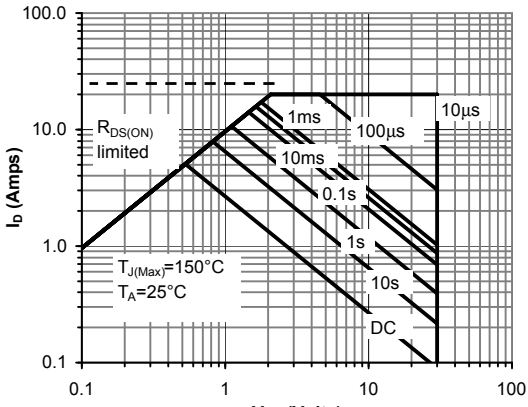


Figure 9: Maximum Biased Safe Operating Area (Note F)

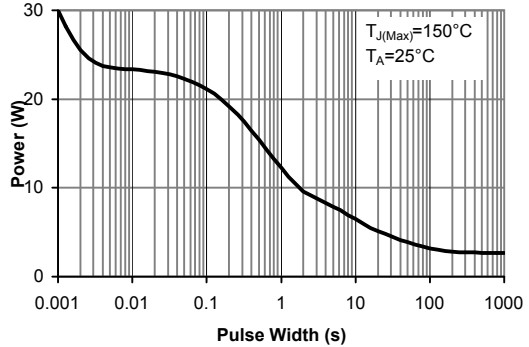


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)

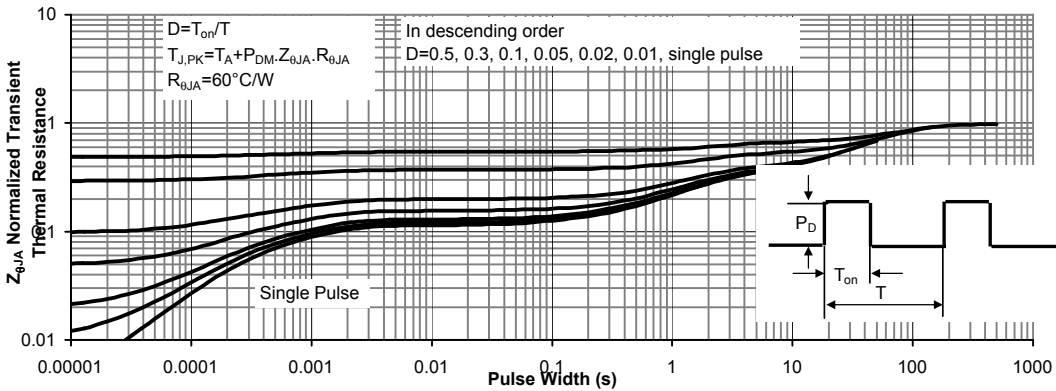
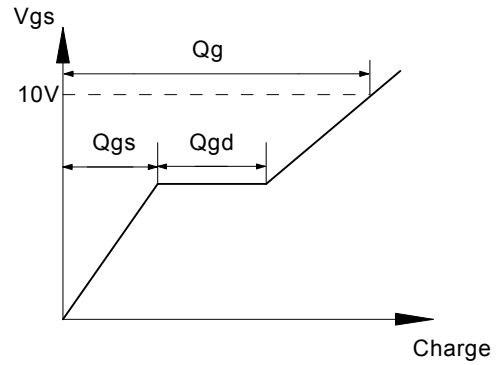
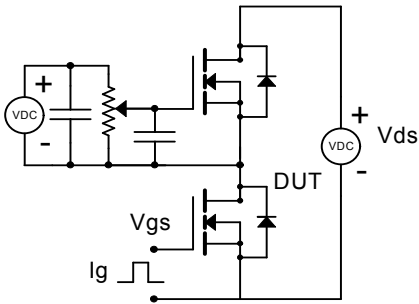
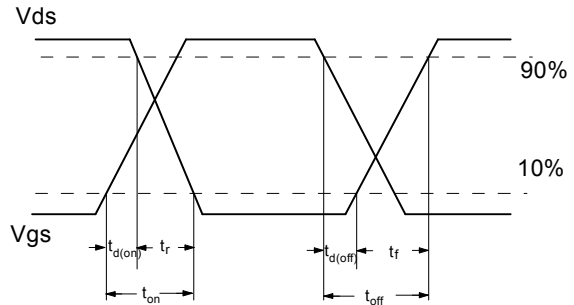
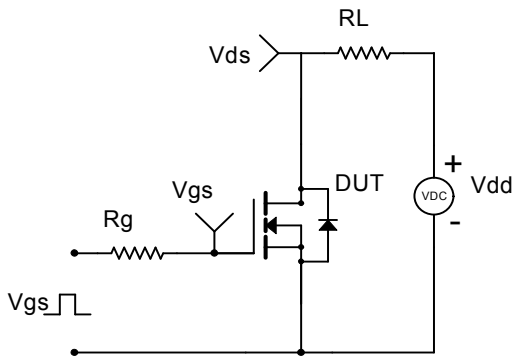


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

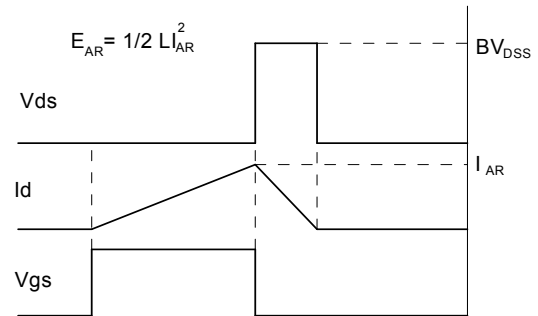
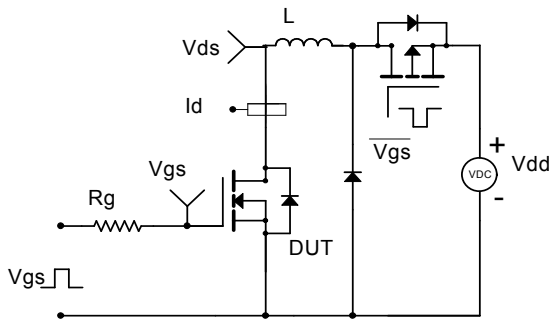
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

